

**Maximum Ratings** (@T<sub>C</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	30	V
Gate-Source Voltage			V <sub>GSS</sub>	±16	V
Continuous Drain Current, V <sub>GS</sub> = 10V (Note 7)	Steady State	T <sub>C</sub> = +25°C T <sub>C</sub> = +100°C	I <sub>D</sub>	240 240	A
Maximum Continuous Body Diode Forward Current (Note 7)			I <sub>S</sub>	100	A
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	400	A
Pulsed Continuous Body Diode Forward Current (380µs Pulse, Duty Cycle = 1%)			I <sub>SM</sub>	400	A
Avalanche Current, L=3mH (Note 8)			I <sub>AS</sub>	15	A
Avalanche Energy, L=3mH (Note 8)			E <sub>AS</sub>	700	mJ

**Thermal Characteristics** (@T<sub>C</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	P <sub>D</sub>	1.2	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R <sub>θJA</sub>	103	°C/W
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	P <sub>D</sub>	2.5	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>θJA</sub>	51	°C/W
Total Power Dissipation (Note 7)	T <sub>C</sub> = +25°C	P <sub>D</sub>	136	W
Thermal Resistance, Junction to Case (Note 7)		R <sub>θJC</sub>	1.1	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +175	°C

**Electrical Characteristics** (@T<sub>C</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b> (Note 9)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250µA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	µA	V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±16V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS</b> (Note 9)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	—	2	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 1mA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	1.25	1.6	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 25A
		—	2	2.5		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 25A
Diode Forward Voltage	V <sub>SD</sub>	—	0.8	1.1	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 25A
<b>DYNAMIC CHARACTERISTICS</b> (Note 10)						
Input Capacitance	C <sub>ISS</sub>	—	5,000	—	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1MHz
Output Capacitance	C <sub>OSS</sub>	—	2,660	—		
Reverse Transfer Capacitance	C <sub>RSS</sub>	—	300	—		
Gate Resistance	R <sub>G</sub>	—	0.75	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>G</sub>	—	37	—	nC	V <sub>DS</sub> = 15V, I <sub>D</sub> = 25A
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>G</sub>	—	77	—		
Gate-Source Charge	Q <sub>GS</sub>	—	10	—		
Gate-Drain Charge	Q <sub>GD</sub>	—	14	—	ns	V <sub>DD</sub> = 15V, V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 25A, R <sub>G</sub> = 4.7Ω
Turn-On Delay Time	t <sub>D(ON)</sub>	—	21	—		
Turn-On Rise Time	t <sub>R</sub>	—	45	—		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	32	—		
Turn-Off Fall Time	t <sub>F</sub>	—	26	—	ns	I <sub>S</sub> = 15A, di/dt = 100A/µs
Body Diode Reverse Recovery Time	t <sub>RR</sub>	—	44	—		
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	—	52	—	nC	

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
  - Thermal resistance from junction to soldering point (on the exposed drain pad).
  - I<sub>AS</sub> and E<sub>AS</sub> rating are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

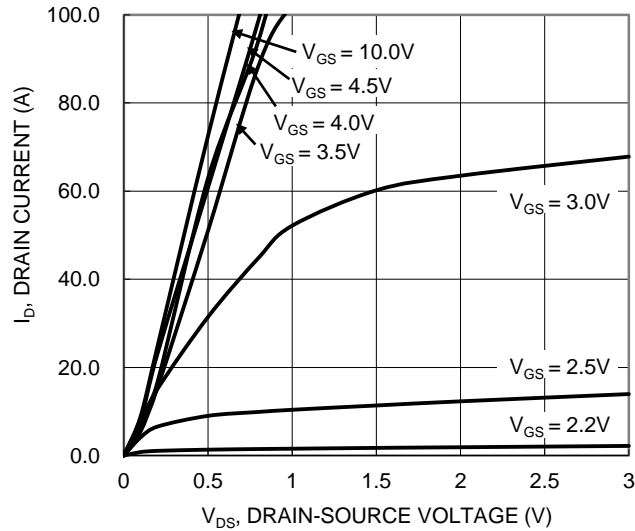


Figure 1. Typical Output Characteristic

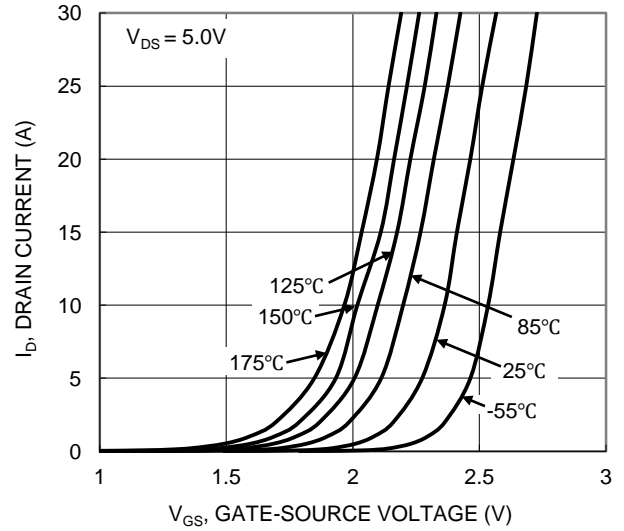


Figure 2. Typical Transfer Characteristic

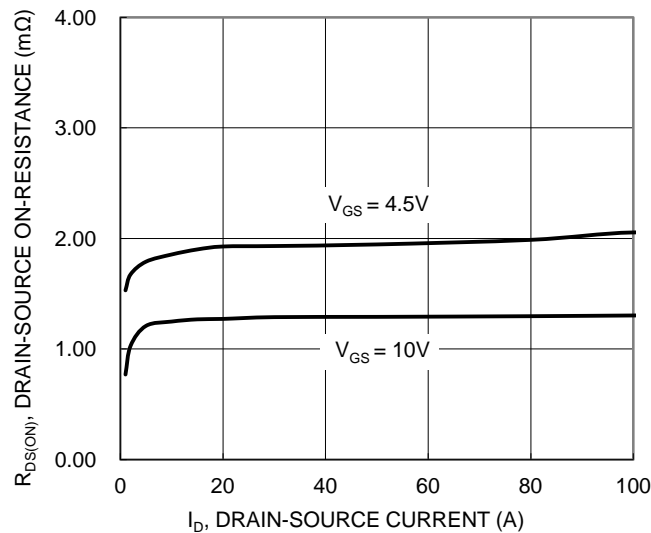


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

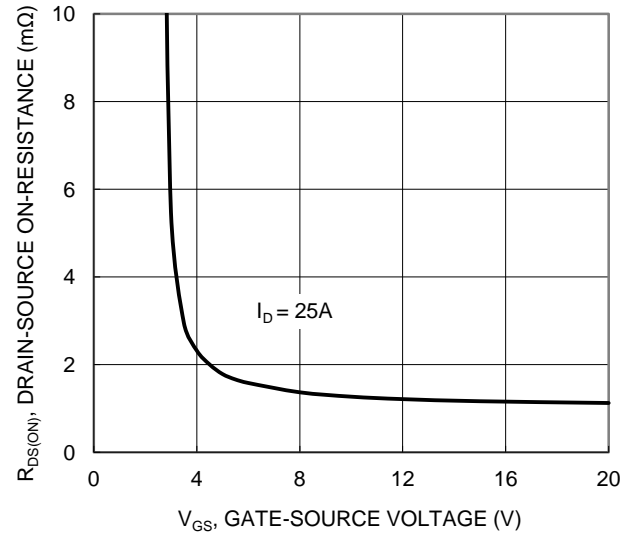


Figure 4. Typical Transfer Characteristic

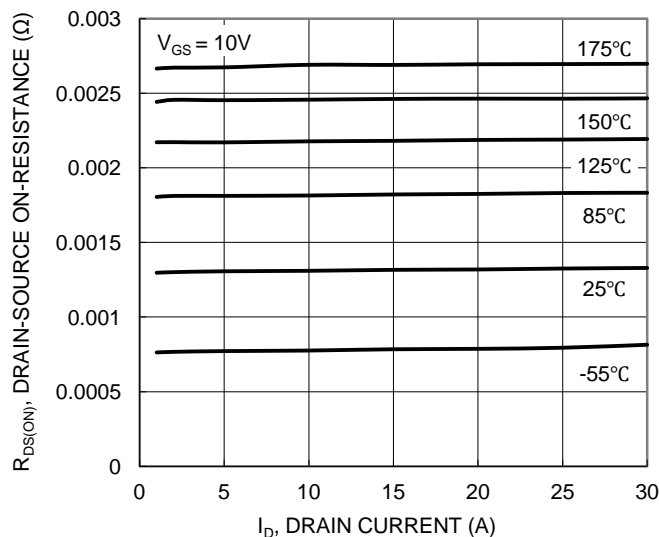


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

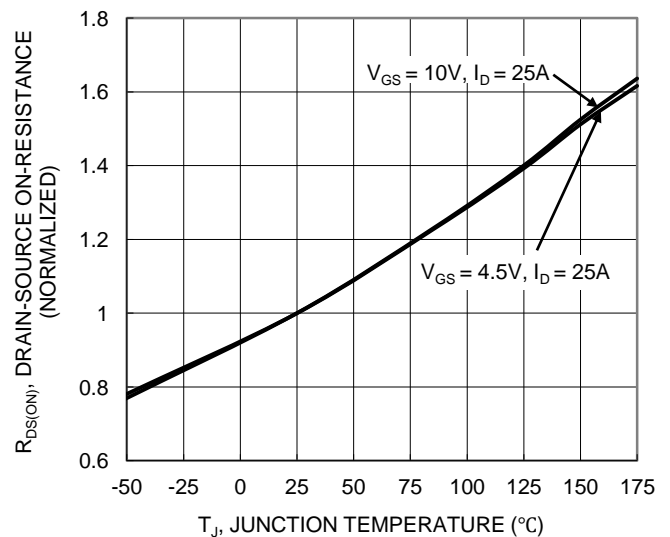


Figure 6. On-Resistance Variation with Temperature

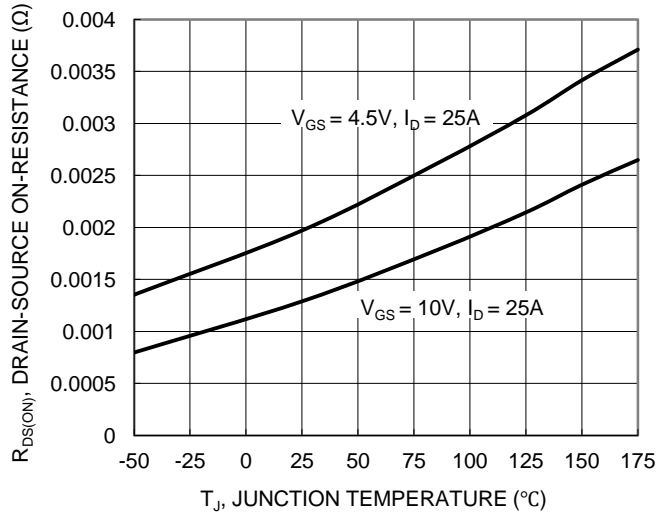


Figure 7. On-Resistance Variation with Temperature

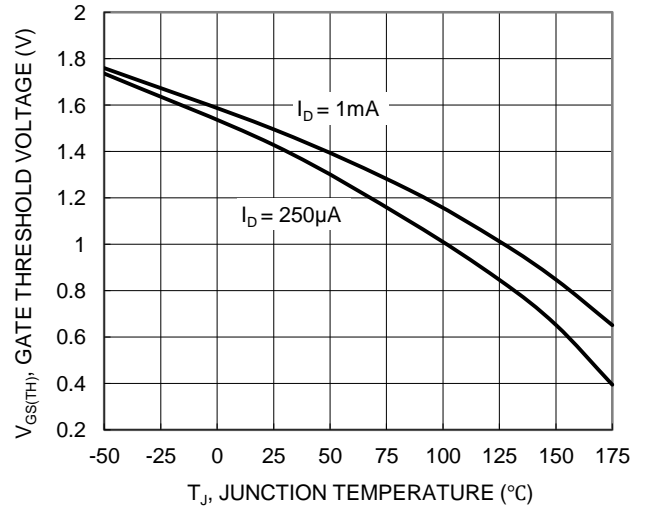


Figure 8. Gate Threshold Variation vs. Junction Temperature

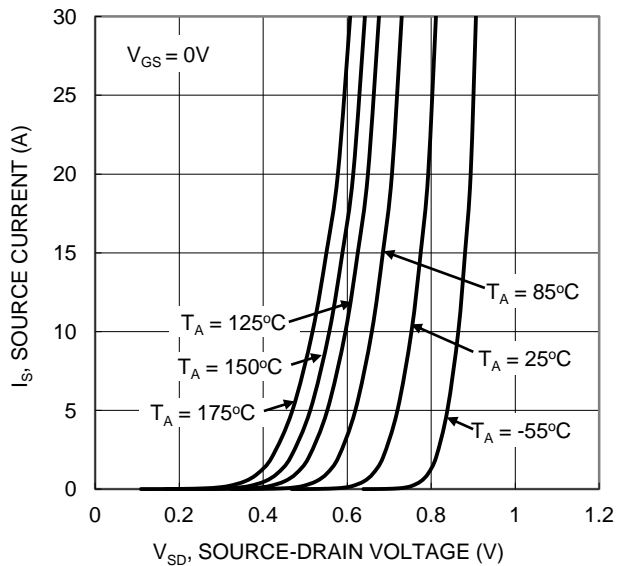


Figure 9. Diode Forward Voltage vs. Current

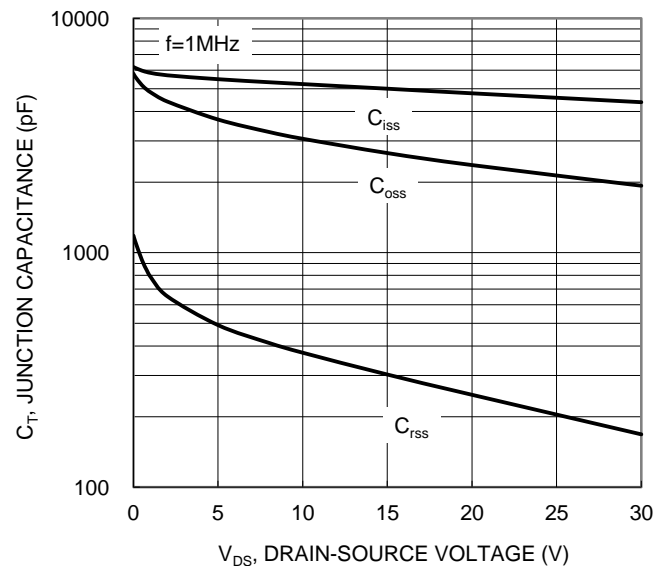


Figure 10. Typical Junction Capacitance

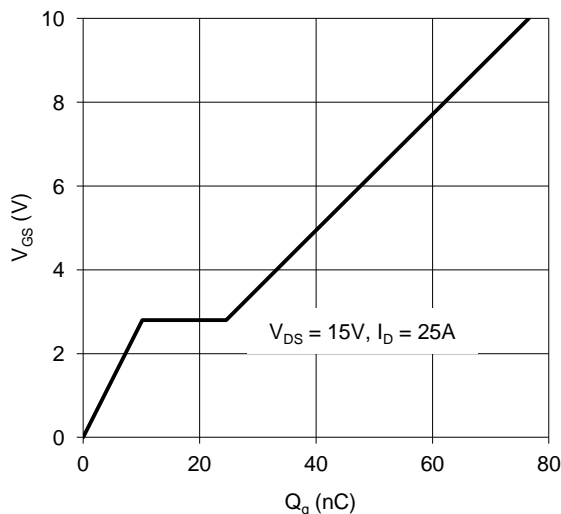


Figure 11. Gate Charge

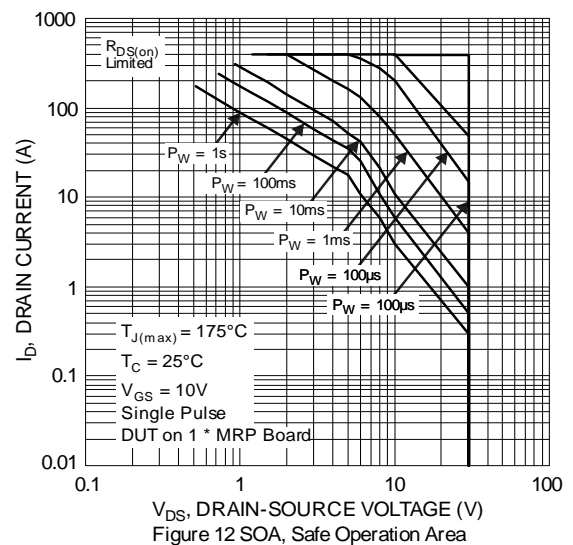


Figure 12 SOA, Safe Operation Area

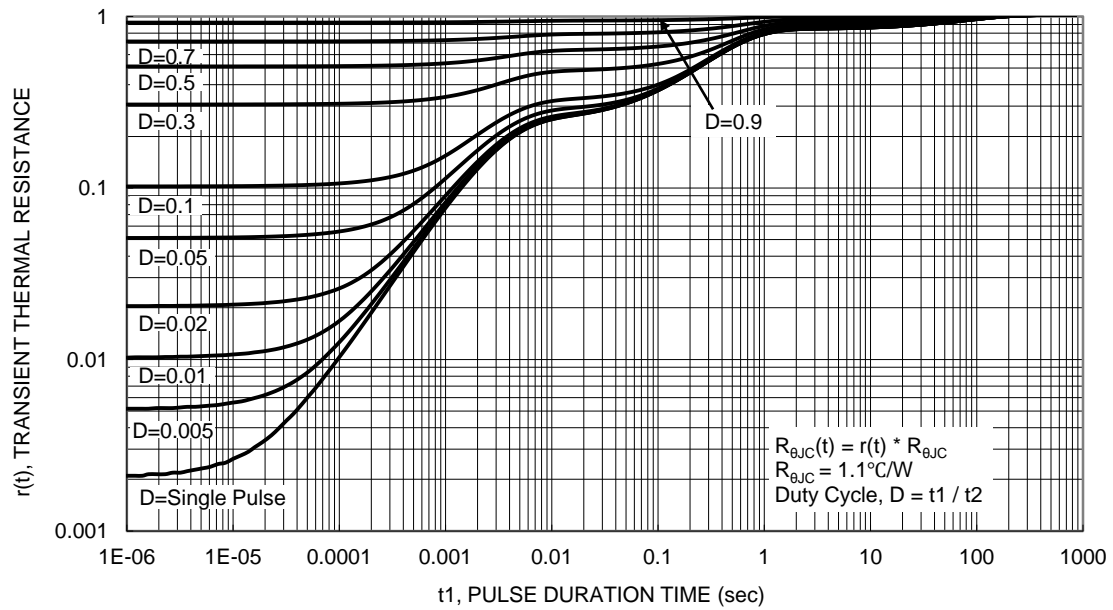
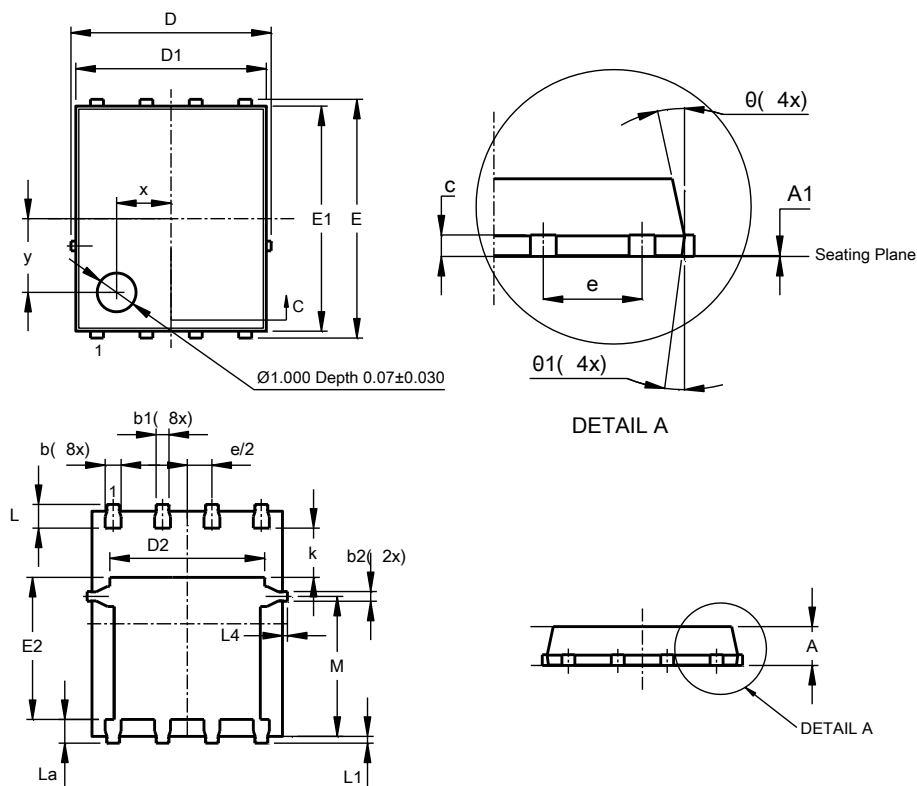


Figure 13. Transient Thermal Resistance

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI5060-8 (Type K)

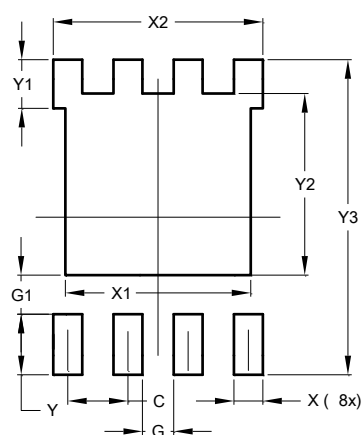


PowerDI5060-8 (Type K)			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0	0.05	0.02
b	0.33	0.51	0.41
b1	0.300	0.366	0.333
b2	0.20	0.35	0.25
c	0.23	0.33	0.277
D	5.15 BSC		
D1	4.85	4.95	4.90
D2	-	-	3.98
E	6.15 BSC		
E1	5.75	5.85	5.80
E2	3.56	3.725	3.66
E	1.27BSC		
k	-	-	1.27
L	0.51	0.71	0.61
La	0.51	0.675	0.61
L1	0.05	0.20	0.175
L4	-	-	0.125
M	3.50	3.71	3.605
x	-	-	1.400
y	-	-	1.900
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI5060-8 (Type K)



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	3.910
X2	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610

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